

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

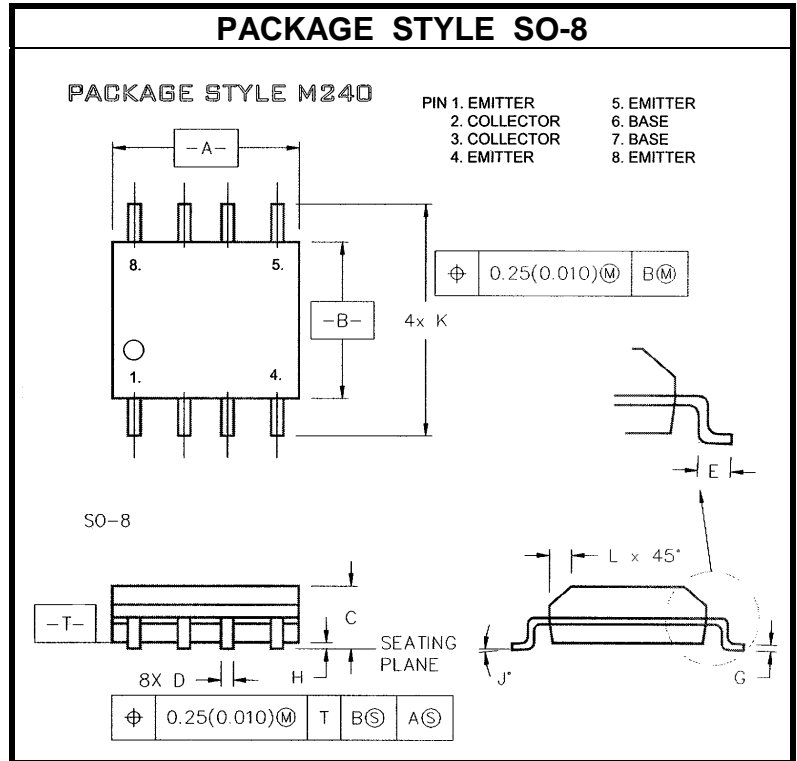
The **ASI MRF5812** is Designed for high current, low power, low noise, amplifiers up to 1.0 GHz.

FEATURES:

- Low Noise – 2.5 dB @ 500 MHz
- Ftau – 5.0 GHz @ 10 V, 75 mA
- Cost Effective SO-8 package

MAXIMUM RATINGS

I_C	200 mA
V_{CB0}	30 V
V_{CEO}	15 V
V_{EBO}	2.5 V
P_{DISS}	1.25 W @ T _C = 25 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA		30			V
BV_{CEO}	I _C = 5.0 mA		15			V
BV_{EBO}	I _E = 0.1 mA		2.5			V
I_{CB0}	V _{CB} = 15 V				0.1	mA
I_{EBO}	V _{CE} = 2.0 V				0.1	mA
h_{FE}	V _{CE} = 5.0 V	I _C = 50 mA	50		200	---
C_{OB}	V _{CB} = 10 V	f = 1.0 MHz		1.4	2.0	pF
F_{TAU}	V _{CE} = 10 V	I _C = 75 mA		5.0		GHz
NF_{min}	V _{CE} = 10 V	I _C = 50 mA	f = 500 MHz	2.0	3.0	dB
G_{NF}				13	15.5	%
G_{U max}				17.8		dB
MSG				20		dB
 S₂₁ ²				15		dB